
2SK1153, 2SK1154

Silicon N-Channel MOS FET

HITACHI

Application

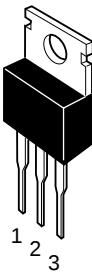
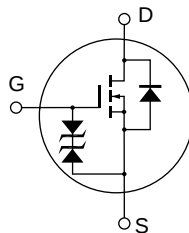
High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- No secondary breakdown
- Suitable for switching regulator and DC-DC converter

Outline

TO-220AB



1. Gate
2. Drain
(Flange)
3. Source

2SK1153, 2SK1154

Absolute Maximum Ratings (Ta = 25°C)

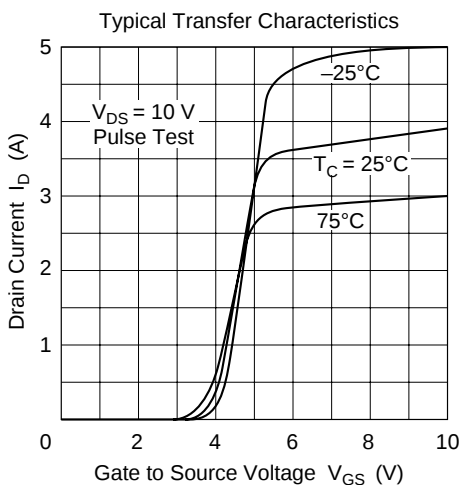
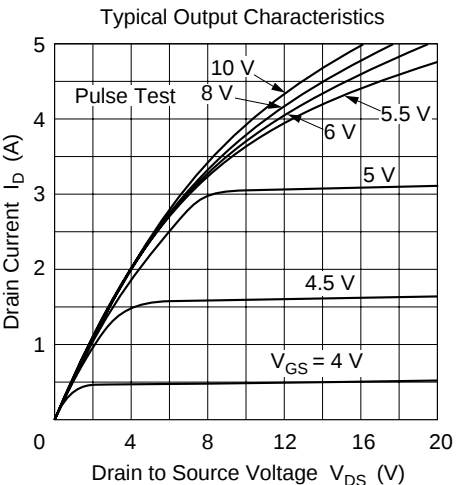
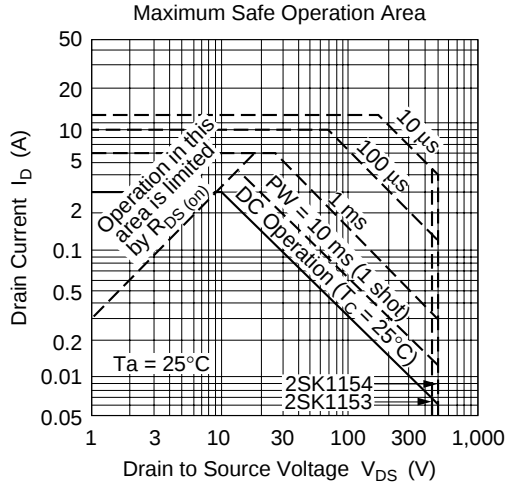
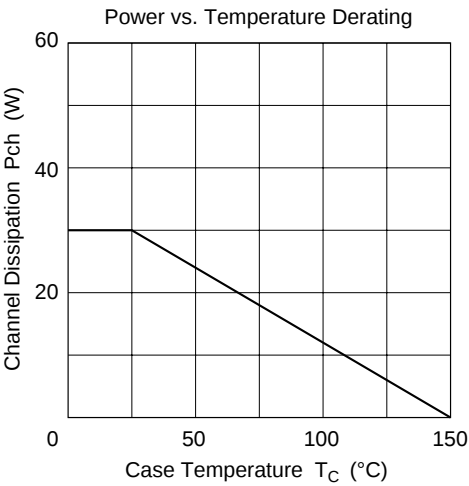
Item		Symbol	Ratings	Unit
Drain to source voltage	2SK1153	V_{DSS}	450	V
	2SK1154		500	
Gate to source voltage		V_{GSS}	±30	V
Drain current		I_D	3	A
Drain peak current		$I_{D(pulse)}^{*1}$	12	A
Body to drain diode reverse drain current		I_{DR}	3	A
Channel dissipation		P_{ch}^{*2}	30	W
Channel temperature		Tch	150	°C
Storage temperature		Tstg	−55 to +150	°C

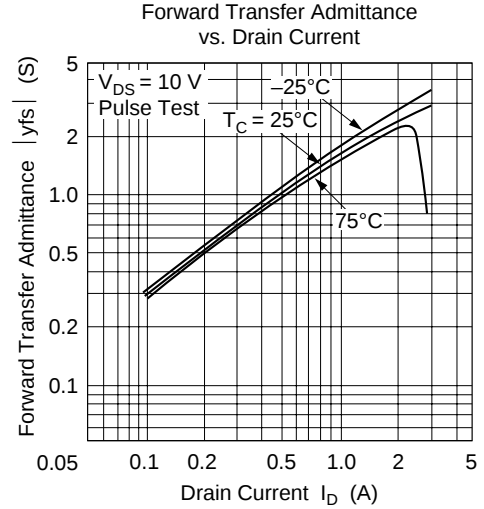
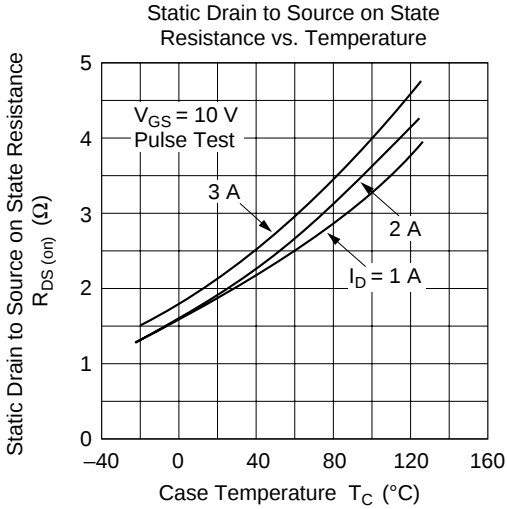
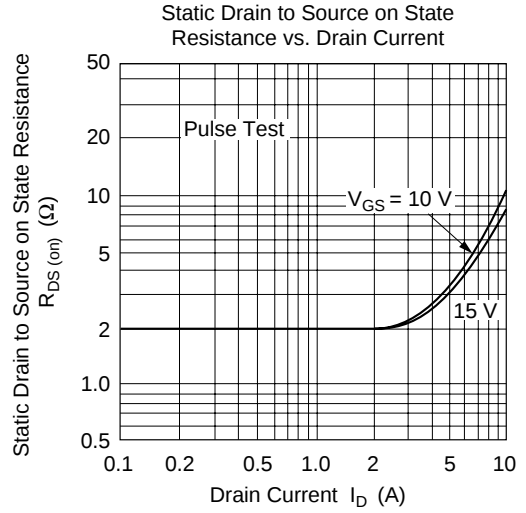
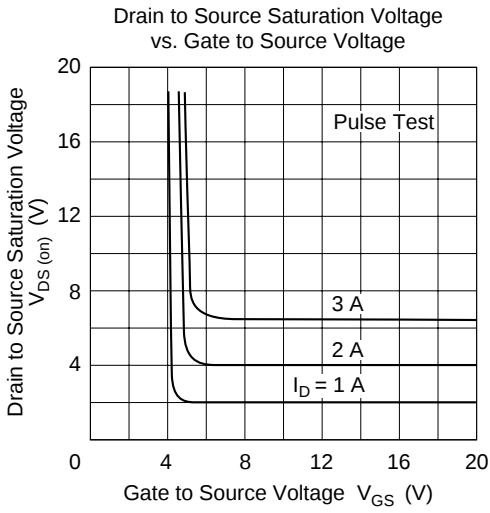
Notes: 1. $PW \leq 10 \mu s$, duty cycle $\leq 1\%$
2. Value at $T_c = 25^\circ C$

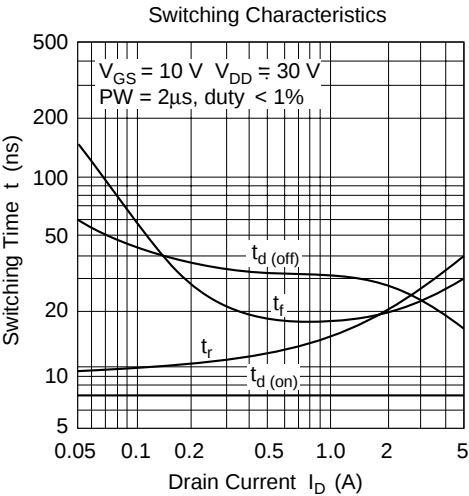
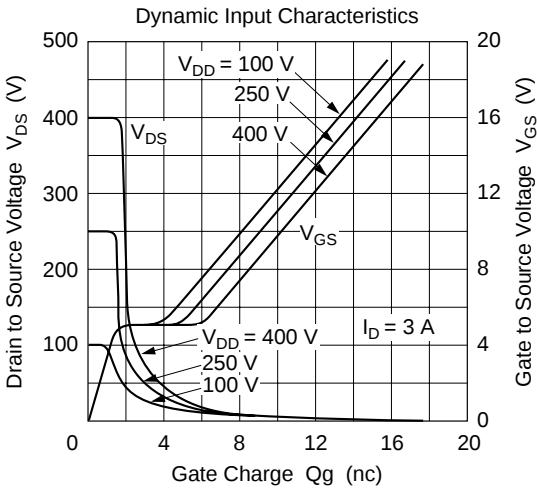
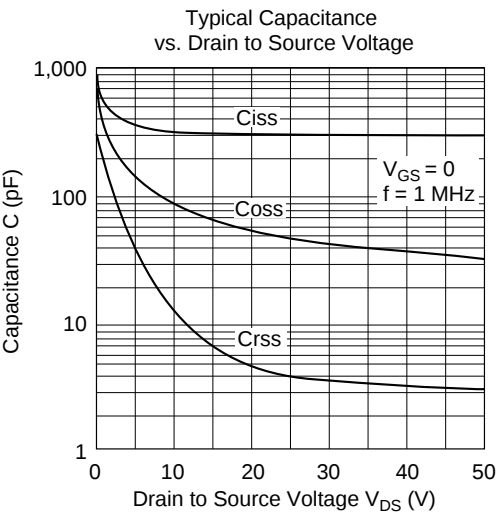
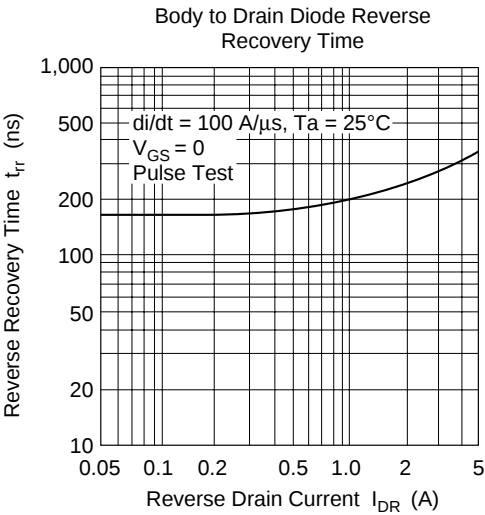
Electrical Characteristics (Ta = 25°C)

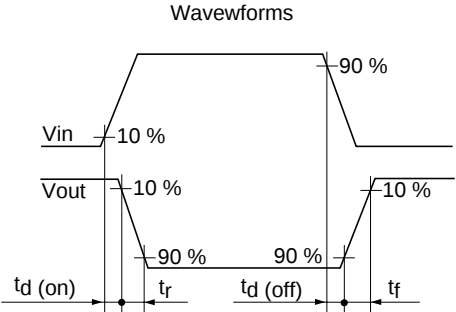
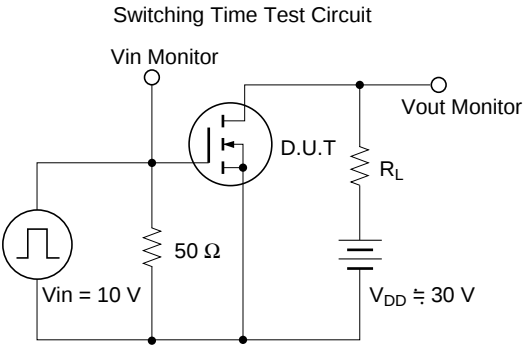
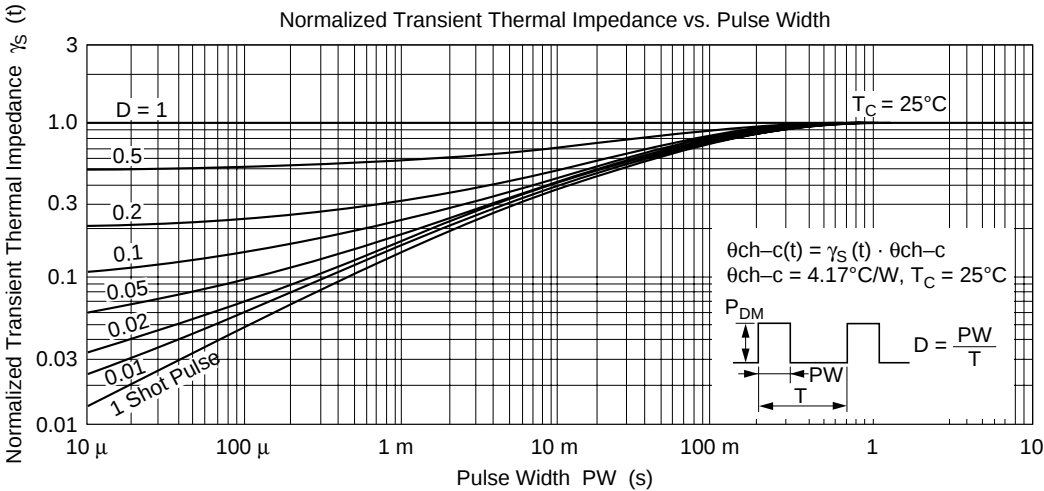
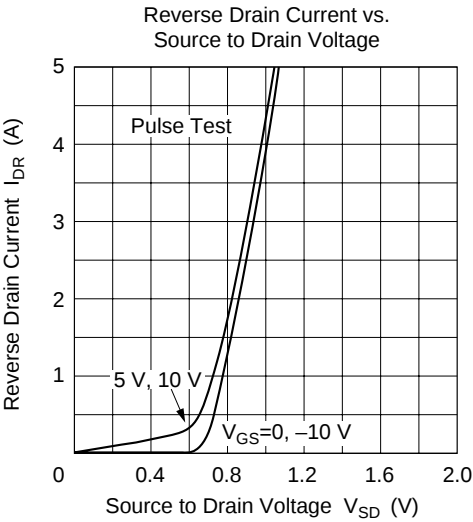
Item		Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	2SK1153 2SK1154	$V_{(BR)DSS}$	450 500	—	—	V	$I_D = 10 \text{ mA}$, $V_{GS} = 0$
Gate to source breakdown voltage		$V_{(BR)GSS}$	± 30	—	—	V	$I_G = \pm 100 \text{ }\mu\text{A}$, $V_{DS} = 0$
Gate to source leak current		I_{GSS}	—	—	± 10	μA	$V_{GS} = \pm 25 \text{ V}$, $V_{DS} = 0$
Zero gate voltage drain current	2SK1153 2SK1154	I_{DSS}	—	—	250	μA	$V_{DS} = 360 \text{ V}$, $V_{GS} = 0$ $V_{DS} = 400 \text{ V}$, $V_{GS} = 0$
Gate to source cutoff voltage		$V_{GS(off)}$	2.0	—	3.0	V	$I_D = 1 \text{ mA}$, $V_{DS} = 10 \text{ V}$
Static Drain to source on state resistance	2SK1153 2SK1154	$R_{DS(on)}$	— —	2.0 2.2	2.8 3.0	Ω	$I_D = 2 \text{ A}$, $V_{GS} = 10 \text{ V}^{*1}$
Forward transfer admittance		$ y_{fs} $	1.5	2.5	—	S	$I_D = 2 \text{ A}$, $V_{DS} = 10 \text{ V}^{*1}$
Input capacitance		C_{iss}	—	330	—	pF	$V_{DS} = 10 \text{ V}$, $V_{GS} = 0$,
Output capacitance		C_{oss}	—	90	—	pF	$f = 1 \text{ MHz}$
Reverse transfer capacitance		C_{rss}	—	15	—	pF	
Turn-on delay time		$t_{d(on)}$	—	7	—	ns	$I_D = 2 \text{ A}$, $V_{GS} = 10 \text{ V}$,
Rise time		t_r	—	20	—	ns	$R_L = 15 \text{ }\Omega$
Turn-off delay time		$t_{d(off)}$	—	30	—	ns	
Fall time		t_f	—	20	—	ns	
Body to drain diode forward voltage		V_{DF}	—	0.9	—	V	$I_F = 3 \text{ A}$, $V_{GS} = 0$
Body to drain diode reverse recovery time		t_{rr}	—	300	—	ns	$I_F = 3 \text{ A}$, $V_{GS} = 0$, $di_F/dt = 100 \text{ A}/\mu\text{s}$

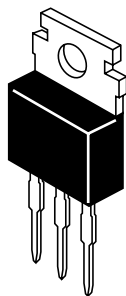
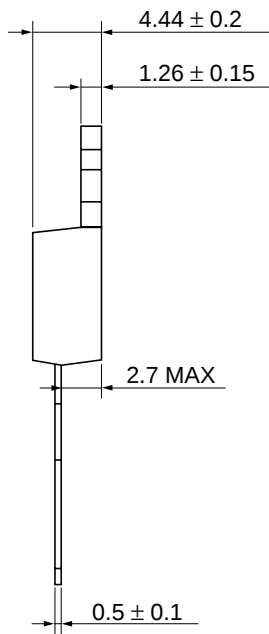
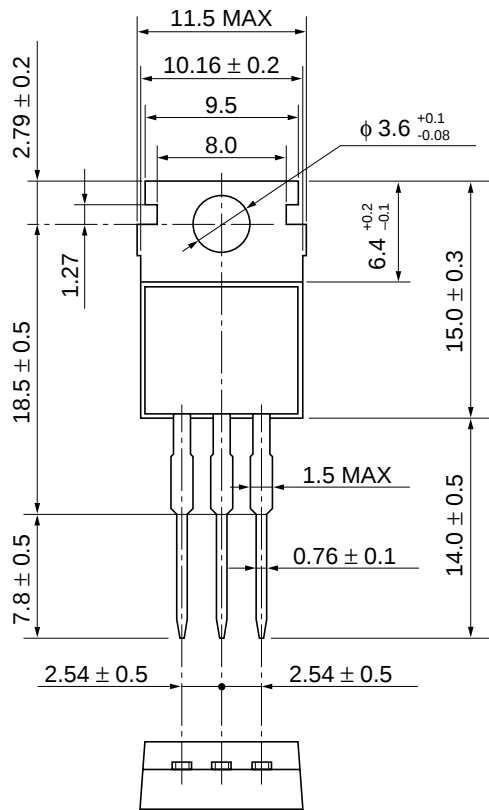
Note: 1. Pulse test











Hitachi Code	TO-220AB
JEDEC	Conforms
EIAJ	Conforms
Weight (reference value)	1.8 g

Cautions

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